EJBF410

SURFACE MOUNT GPP SUPER FAST RECOVERY BRIDGE RECTIFIER

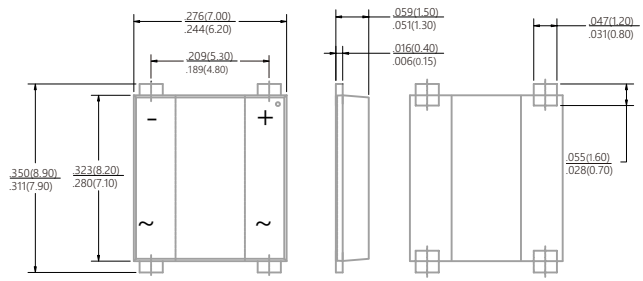
Reverse Voltage: 1000 Volts
Forward Current: 4. 0 Amps

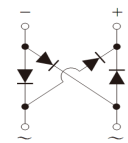
SEMICONDUCTOR

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Glass passivated chip junction
- High surge forward current capability
- Fast reverse recovery time
- High temperature soldering guaranteed:260°C/10 seconds at terminals
- Component in accordance to RoHS 2011/65/EU
- Chip Size:95mil

JBF





Dimensions in inches and (millimeters)

APPLICATIONS

- Case: JBF molded plastic body
- Terminals: Plated leads solderable per MIL-STD-202,method 208
- Mounting Position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Rating at 25°C ambient temperature unless otherwise specified. Single phase ,half wave ,60Hz,resistive or inductive load. For capacitive load,derate current by 20%.)

Parameters	Symbols	Value	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	1000	Volts
Maximum RMS Voltage	V_{RMS}	700	Volts
Maximum DC Blocking Voltage	V_{DC}	1000	Volts
Maximum Average Forward Rectified Current	$I_{(AV)}$	4. 0	Amp
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	100	Amps
Rating for fusing(@8.3ms)	I^2t	41.5	A^2s
Forward Voltage @IF=4. 0A	V_F	1. 6	Volts
Reverse Current @TA=25°C @TA=125°C	I_R	5 100	μA
Maxmum Reverse Recovery Time(Note2)	trr	75	ns
Typical Junction Capacitance(Note1)	Cj	62	pF
Typical thermal resistence	$R_{\theta JC}$	10	°C/W
Operating temperature range	T_J	-55 to +150	°C
Storage temperature range	T_{STG}	-55 to +150	°C

Note:1 Measured at 1 MHZ and applied reverse voltage of 4V D.C
2 Measured with I_F=0.5A,I_R=1A,I_{rr}=0.25A

RATINGS AND CHARACTERISTIC CURVES EJBF410

FLG.1-MAXIMUM FORWARD SUNRGE CURRENT

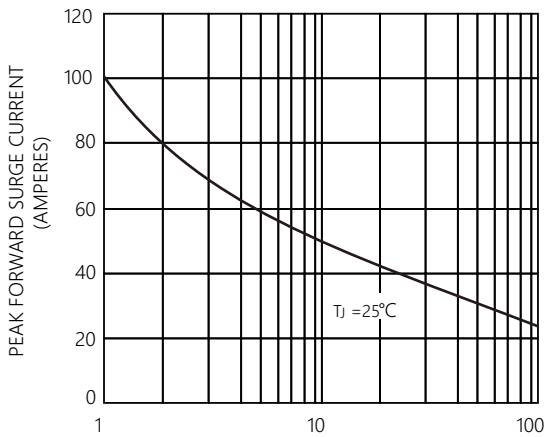


FIG.2-FORWARD CURRENT DERATING CURVE

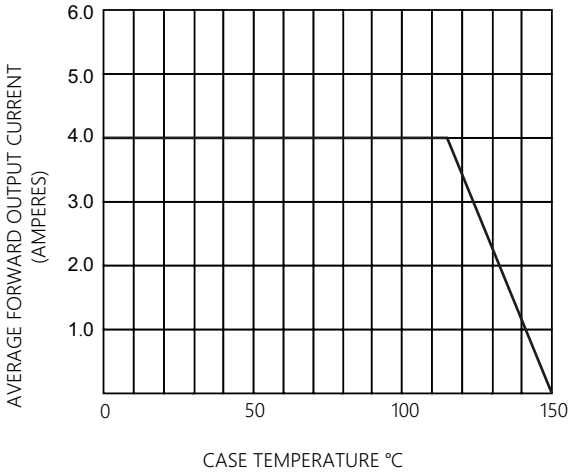


FIG.3-TYPICAL FORWARD CHARACTERISTICS

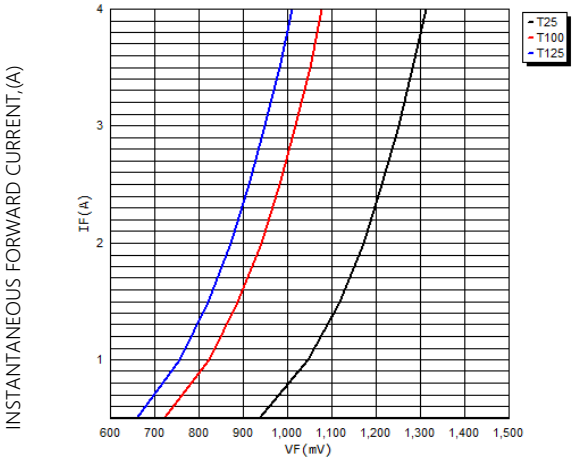


FIG.4 -TYPICAL REVERSE CHARACTERISTICS